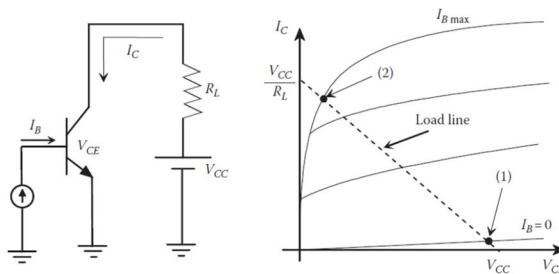


EX 1 Bipolar Transistor

A bipolar transistor is used in the circuit below, $V_{CC} = 40 \text{ V}$ and the load resistance $R_L = 10\Omega$. In the saturated region, the collector-emitter voltage $V_{CE} = 0,1 \text{ V}$ and the current gain of the base $\beta = 5$. Calculate the following numerical values

- a) The current and power of the load.
- b) The losses in the collector circuit.
- c) The losses in the base circuit, when the base-emitter junction is a diode with a voltage drop $V_{BE}=0,7 \text{ V}$
- d) The efficiency of the whole circuit.



EX 2 Bipolar Transistor

In the previous circuit the system is working in an operating point where the collector current $I_c = 2 \text{ A}$. Calculate the power of the load resistance and the efficiency of the system.

EX 3 Diode Bridge

A single-phase diode bridge is supplied from 50 Hz ac system where the rms value of the voltage is 230 V and its peak value $\sqrt{2} * 230 \text{ V}$. The load of the rectifier is a 10Ω resistance.

- a) Draw the waveforms of the dc voltage and current and calculate their average values.
- b) Calculate the power delivered to the resistance.

EX 4 Diode Bridge

A single-phase diode bridge is supplied from 50 Hz ac system where the rms value of the voltage is 230 V. The load of the rectifier is a 10Ω resistance. However, now we are assuming that the dc side has a large filtering inductance and therefore the dc side current is ideal dc. With this assumption, repeat the questions in EX 3, i.e.

- a) Draw the waveforms of the dc voltage and current and calculate their average values.
- b) Calculate the power delivered to the resistance.